

**IN THE SPECIFICATION:**

Please replace paragraph [0077] with the following amended paragraph:

[0077] A silicon oxycarbide material is deposited from an oxidized organosilicon compound by the process described herein, as an interlayer dielectric material, such as the first dielectric layer 510. A first silicon carbide barrier layer 512 is generally deposited on the substrate surface to eliminate inter-level diffusion between the substrate and subsequently deposited material. The first silicon carbide barrier layer 512 may be a nitrogen containing silicon carbide layer deposited by introducing a silicon source gas, a carbon source gas, a nitrogen source gas, and a noble gas, generating a plasma in the processing chamber, and reacting the silicon source gas, the carbon source gas, the nitrogen source gas, and the noble gas to deposit the first silicon carbide barrier layer 512. A capping layer 513 of nitrogen free silicon carbide ~~(not shown)~~ may be deposited in situ on the first silicon carbide barrier layer 512 by minimizing or eliminating the nitrogen source gas.

Please replace paragraph [0081] with the following amended paragraph:

[0081] As shown in Figure 4A, a first silicon carbide barrier layer 512 is deposited on the substrate surface. The silicon carbide material of the first silicon carbide barrier layer 512 may be doped with nitrogen. ~~While not shown a~~ A capping layer 513 of nitrogen free silicon carbide may be deposited on the barrier layer 512. The nitrogen free silicon carbide may be deposited in situ by the nitrogen doped silicon carbide process with the source of nitrogen minimized or eliminated during the deposition process.

Please replace paragraph [0086] with the following amended paragraph:

[0086] The low k etch stop 514 ~~is~~ and the capping layer 515 are then pattern etched to define the contact/via openings 516 and to expose first dielectric layer 510 in the

areas where the contacts/vias are to be formed as shown in Figure 4C. Preferably, low k etch stop 514 is pattern etched using conventional photolithography and etch processes using fluorine, carbon, and oxygen ions. ~~While not shown, a nitrogen-free silicon carbide or silicon oxide cap layer between about 100 and about 500 may be deposited on the etch stop 516 prior to depositing further materials.~~

Please replace paragraph [0087] with the following amended paragraph:

[0087] After low k etch stop 514 ~~has~~ and the capping layer 515 have been etched to pattern the contacts/vias and the photoresist has been removed, a second dielectric layer 518 of silicon oxycarbide from an oxidized organosilane or organosiloxane by the process described herein, such as trimethylsilane, is deposited to a thickness of about 5,000 to about 15,000 Å as shown in Figure 4D.